



Development (un-exposed region removal)



**Figure 4-2** Proposed e-beam lithography process for the fabrication of damascene structure.



**Figure 4-3** FTIR spectra of HSQ during traditional thermal baking and furnace curing processes.



**Figure 4-4** The (a) cage-like and (b) network-like structures of HSQ.



**Figure 4-5** FTIR spectra of HSQ films with different doses of electron beam exposure, ranging from 100 uC/cm<sup>2</sup> to 700 uC/cm<sup>2</sup>.



**Figure 4-6** The leakage current densities of e-beam exposed HSQ films at different doses.



**Figure 4-8** The SEM cross-sectioned profile of collapsed pattern for dense HSQ lines.

X34.9K

25.0kV

์5 n m

5

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**Figure 4-10** The SEM micrograph of patterned HSQ film with critical dimensions of 60 nm.



 Figure 4-11
 The comparison of dielectric constants of e-beam exposed HSQ films with different treatment.



**Figure 4-12** Leakage current of e-beam exposed HSQ with TMAH development followed by thermal annealing, as compared to typical furnace cured HSQ films.



**Figure 4-13** Temperature dependence of moisture desorption from HSQ films with e-beam exposed HSQ followed by TMAH developed and thermal annealed processes and with furnace curing.

